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Proceedings of the International Semiconductor Conference, CAS, 2010, vol.2, pages 371-374

Temperature dependence of capture coefficients in trapping phenomena

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Abstract

The temperature dependence of the capture coefficients in trapping phenomena is investigated. It is proved that, besides the dependence induced by the thermal velocity of the carriers, the stress-induced traps at the interfaces of the multi-layered structures present a supplementary temperature dependence. This dependence is found to be of Gaussian type and is in a good agreement with the experimental results. © 2010 IEEE.

http://dx.doi.org/10.1109/SMICND.2010.5649094

Keywords

Capture coefficients, Gaussian distribution, Relaxation currents, Traps